

3) Amendments to the Specification

Please amend the paragraph beginning on page 2, line 11, as follows:

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These problems are generally solved or circumvented by the present invention, which achieves technical advantages as a method of simultaneously forming top and bottom plates of a MIM capacitor. A first resist is used to provide the pattern for the bottom metal plate, and a second resist is used to provide the pattern for the top metal plate of a MIM capacitor. The combined patterns of the first and second resist are is simultaneously transferred to the underlying metallization layers in a single reactive ion etch (RIE) process.

Please amend the paragraph beginning on page 4, line 16, as follows:

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A description of preferred embodiments of the present invention will be discussed, followed by some advantages thereof. Four MIM capacitors are shown in each figure, although many MIM capacitors and other conductive lines may be present within each layer.